

## Transmitter Specifications

**Table 32 Transmitter Specifications**

Property	Description / Value
Laser source	Indium Gallium Arsenide (InGaAs) Diode Laser
Center wavelength	910 ± 10 nm at 25 °C (77 °F)
Operating Mode	Pulsed
Nominal pulse properties at full range measurement:	
Energy	1.2 μWs ± 20 % (factory adjustment)
Peak power	11 W typical
Width, 50 %	110 ns typical
Repetition rate	10.0 kHz
Average power	12.0 mW
Max Irradiance	760 μW/cm <sup>2</sup> measured with 7 mm aperture
Laser classification	Classified as Class 1M laser device in accordance with IEC/EN 60 825-1 Complies with 21 CFR 1040.10 and 1040.11 except for the deviations pursuant to the Laser Notice No. 50, dated July 26, 2001.
Beam divergence	±0.4 mrad x ±0.7 mrad

## Receiver Specifications

**Table 33 Receiver Specifications**

Property	Description / Value
Detector	Silicon Avalanche Photodiode (APD)
Surface diameter	0.5 mm (0.02 in.)
Receiver bandwidth	3 MHz (-3db)
Interference filter	Center wavelength 915 nm typical
50 % pass band	36 nm
Transmissivity at 913 nm	80 % typical
Field-of-view divergence	± 0.83 mrad

## Optical System Specifications

**Table 34 Optical System Specifications**

Property	Description / Value
Optics System Focal Length	300 mm (11.8 in.)
Effective lens diameter	96 mm (3.8 in.)
Lens transmittance	96 % typical
Window transmittance	97 % typical, clean